

INDUCTIVE LOAD TESTER (Included leakage current test) リーク電流測定機能付き L 負荷テスター

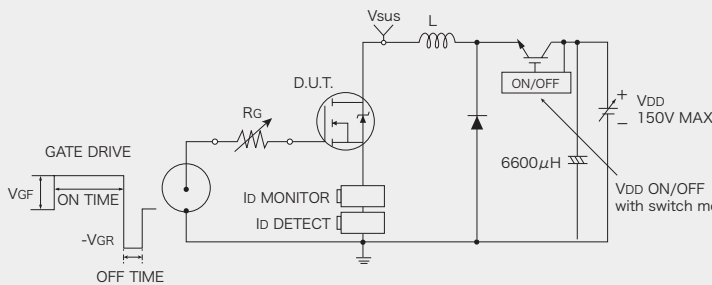
LVNI20ZFCC

150V
200A

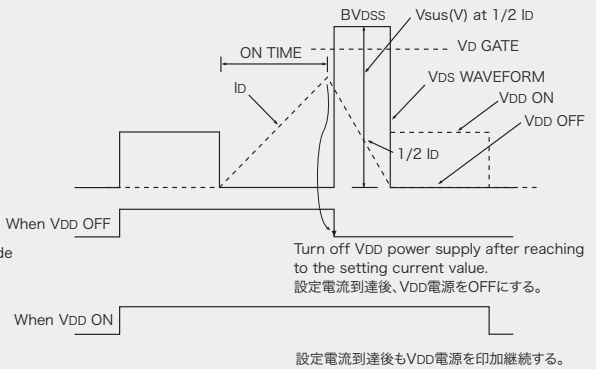
● LVNI20ZFCC is inductive load tester for MOS-FET, which system is for a measurement with a wafer condition. This system is equipped with high speed interception circuits at a chip destruction, and has IGSS and IDSS measurement circuits for leakage measurement before and after L load measurement.

● LVNI20ZFCC は、MOS-FET 専用の L 負荷試験器で、ウェハ状態での測定に対応したシステム構成となっています。チップ破壊時の高速遮断回路を装備するとともに、IGSS、IDSS の測定回路を実装しており、L 負荷試験前後のリーク測定も可能としています。

Test Circuit



Measurement Waveform



MODEL LVNI20ZFCC

SETTING RANGE

MEASURABLE DEVICES

N/P MOS-FET

ID/IL	±0.20A~±9.99A	0.01A STEP
	±02.0A~±99.9A	0.1A STEP
	±020A~±200A	1A STEP
VDD	±001V~±150V	1V STEP
VGF	±00.1V~±20.0V	0.1V STEP
VGR	±00.1V~±20.0V	0.1V STEP
REPEAT	1~19	
ON TIME	0.0000ms~2.0000ms	0.1µs STEP
OFF TIME	01.0ms~10.0ms	0.1ms STEP
DET-DELAY	0.1µs~9.9µs	0.1µs STEP
V-GATE	0.001kV~1.999kV	1V STEP
Rg	6 circuit select	

BINNING

BIN INDICATION PASS, PRE-FAIL, POST-FAIL, Vd-FAIL, ID-ERROR, SELF-FAIL

DIMENSIONS & WEIGHT

MAIN UNIT	500(W)×800(D)×900(H)…130kg
HEAD BOX	430(W)×700(D)×245(H)…32kg

LEAKAGE CURRENT

SETTING RANGE

IDSS	Voltage(VDs): 0.01V~99.9V	Current: 00.00nA~99.99µA
IGSS	Voltage(VGs): 0.01V~99.9V	Current: 00.00nA~99.99µA

[Wafer map display]

[ウエハマップ表示]

